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40V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} Max	I _D T _A = +25°C
40V	$27m\Omega$ @ $V_{GS} = 10V$	7.1A
40 V	$47m\Omega$ @ $V_{GS} = 4.5V$	5.4A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features and Benefits

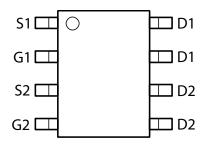
- Low on-resistance
- Fast switching speed
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

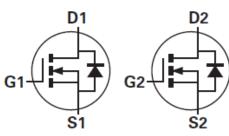
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (approximate)







Top View



Equivalent Circuit

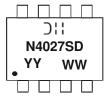
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN4027SSD-13	Standard	SO-8	2500 / Tape & Reel
DMN4027SSDQ-13	Automotive	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information





O|| = Manufacturer's Marking N4027SD = Product Type Marking Code for DMN4027SSD-13 N4027DQ = Product Type Marking Code for DMN4027SSDQ-13 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage		(Note 5)	V _{GS}	±20	V
		(Notes 7)		7.1	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70$ °C (Notes 7)	I _D	5.7	Α
		(Notes 6)		5.4	
Pulsed Drain Current	$V_{GS} = 10V$	(Notes 8)	I _{DM}	28.0	Α
Continuous Source Current	(Body diode)	(Notes 7)	Is	3.3	Α
Pulsed Source Current (Bod	y diode)	(Notes 8)	I _{SM}	28.0	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 6 & 9)	1.25 10.0			
Power Dissipation Linear Derating Factor	(Notes 6 & 10)	P_{D}	1.8 14.3	W mW/°C	
	(Notes 7 & 9)		2.14 17.2		
	(Notes 6 & 9)		100	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6 & 10)	$R_{ hetaJA}$	70		
	(Notes 7 & 9)		58		
Thermal Resistance, Junction to Lead	(Notes 9 & 11)	$R_{ heta JL}$	53		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

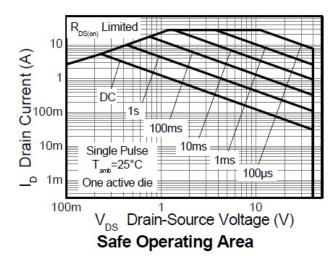
Notes:

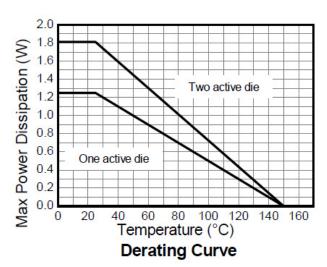
- 5. AEC-Q101 V_{GS} maximum is $\pm 16 \text{V}.$
- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as note (3), except the device is measured at $t \le 10$ sec.
- Same as note (3), except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
 For a dual device with one active die.

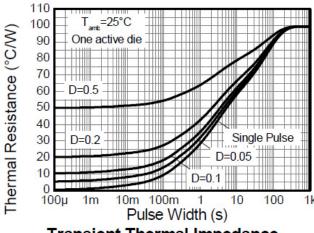
- 10. For a device with two active die.11. Thermal resistance from junction to solder-point (at the end of the drain lead).

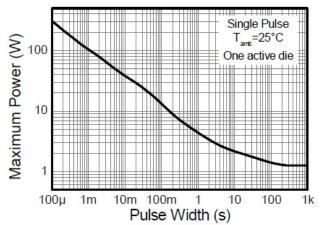


Thermal Characteristics









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μΑ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$I_D=250\mu A,\ V_{DS}=V_{GS}$	
Static Drain-Source On-Resistance (Note 12)	Б		0.017	0.027	Ω	V _{GS} = 10V, I _D = 7A	
Static Dialif-Source Off-Nesistance (Note 12)	R _{DS(ON)}	_	0.031	0.047	12	$V_{GS} = 4.5V$, $I_D = 6A$	
Forward Transconductance (Notes 12 & 13)	9fs	_	22.8	_	S	V _{DS} = 15V, I _D = 7A	
Diode Forward Voltage (Note 12)	V _{SD}	_	0.86	1.1	V	I _S = 7A, V _{GS} = 0V	
Reverse recovery time (Note 13)	t _{rr}		12.1	_	ns	I _S = 2.1A, di/dt = 100A/μs	
Reverse recovery charge (Note 13)	Q _{rr}	_	5.1	_	nC		
DYNAMIC CHARACTERISTICS (Note 13)							
Input Capacitance	C _{iss}	_	604	_	pF	V _{DS} = 20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	106	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	59.6	_	pF] = 11W112	
Total Gate Charge (Note 14)	Qg	_	6.3	_	nC	V _{GS} = 4.5V	
Total Gate Charge Note 14)	Qg	_	12.9	_	nC	V _{DS} = 20V	
Gate-Source Charge Note 14)	Qgs	_	2.4	_	nC	V _{GS} = 10V	
Gate-Drain Charge Note 14)	Q _{gd}	_	3.3	_	nC		
Turn-On Delay Time Note 14)	t _{D(on)}	_	3.1	_	ns		
Turn-On Rise Time Note 14)	t _r	—	3.1	_	ns	$V_{DD} = 20V$, $V_{GS} = 10V$ $I_D = 1A$, $R_G \approx 6.0\Omega$	
Turn-Off Delay Time (Note 14)	t _{D(off)}	—	15.4	—	ns		
Turn-Off Fall Time Note 14)	t _f	_	7.5	_	ns		

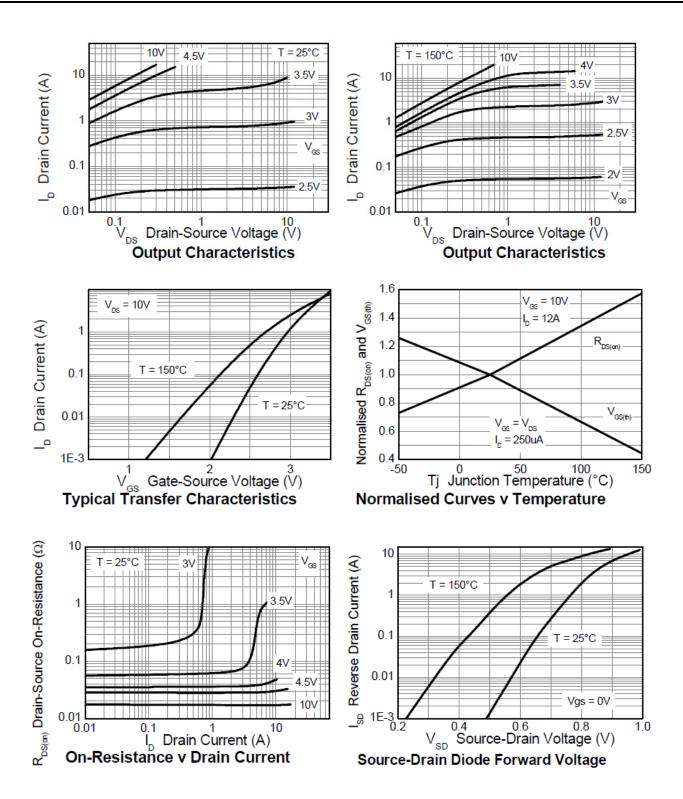
Notes:

^{12.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.



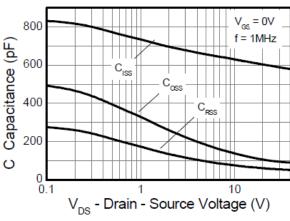


Typical Characteristics

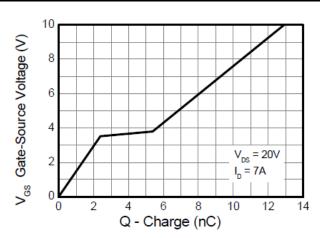




Typical Characteristics (cont.)

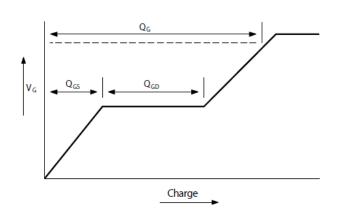


Capacitance v Drain-Source Voltage

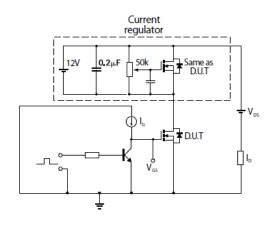


Gate-Source Voltage v Gate Charge

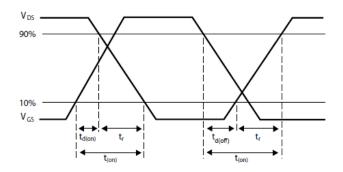
Test Circuits



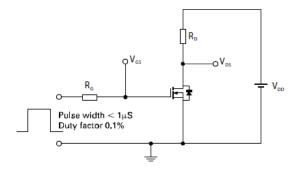
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

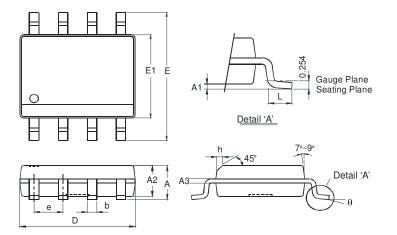


Switching time test circuit



Package Outline Dimensions

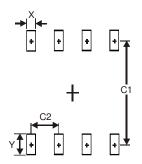
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A 1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	1	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Υ	1.55
C1	5.4
C2	1.27





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